

L Number	Hits	Search Text	DB	Time stamp
1	1228	polynorbornene	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:33
2	1	("6077792").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:31
3	0	polynorbornene and ("6077792").PN.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:34
4	8	foamed near3 polynorbornene	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:46
5	0	NORSOREX and ("6077792").PN.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:37
6	0	avatrel and ("6077792").PN.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:37
7	37	foam\$3 with polynorbornene	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:38
8	6	foam\$3 with polynorbornene and chip	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:39
9	8	foam\$3 with polynorbornene and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:39
10	2	(foam\$3 with polynorbornene and semiconductor) and (foam\$3 with polynorbornene and chip)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:39
11	34	foamed with \$norbornene	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:49
12	8	foamed with \$norbornene and (semiconductor IC chip multichip)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/03/22 10:49

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	769	(xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)	USPAT	2004/03/21 22:35
2	BRS	311	((xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)) and (semiconductor or die or chip or IC)	USPAT	2004/03/21 22:30
3	BRS	1	((xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)) and (semiconductor or die or chip or IC)) and 257/777	USPAT	2004/03/21 21:28
4	BRS	38	((xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)) and (semiconductor or die or chip or IC) with (stack\$2 or mount\$3)	USPAT	2004/03/21 22:31
5	BRS	64	((xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)) and (semiconductor or die or chip or IC) with multi\$4	USPAT	2004/03/21 22:31
6	BRS	1	257/777 and (xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)	USPAT	2004/03/21 22:35
7	BRS	2	(438/108 or 438/109 or 361/760) and (xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)	USPAT	2004/03/21 22:38
8	BRS	3	(257/777 or 438/108 or 438/109 or 361/760) and (xerogels or porous) with (air or voids) with (insulat\$3 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/21 22:39
9	BRS	15	(257/777) and (xerogels or porous) with (insulat\$3 or dielectric)	USPAT	2004/03/21 22:48
10	BRS	102	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric)	USPAT	2004/03/21 22:55

	Type	Hits	Search Text	DBs	Time Stamp
11	BRS	121	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue)	USPAT	2004/03/21 23:02
12	BRS	19	((lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue)) not ((lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric))	USPAT	2004/03/21 22:56
13	BRS	183	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)	USPAT	2004/03/22 00:18
14	BRS	62	((lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)) not ((lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue))	USPAT	2004/03/21 23:02
15	BRS	21	257/777 and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)	USPAT	2004/03/21 23:12

	Type	Hits	Search Text	DBs	Time Stamp
16	BRS	961	(stack\$3 or mount\$3) with (semiconductor or chip or die or IC) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)	USPAT	2004/03/21 23:39
17	BRS	58	(stack\$3 or mount\$3) with (semiconductor or chip or die or IC) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)	JPO	2004/03/22 02:47
18	BRS	1008	(multi\$5) with (semiconductor or chip or die or IC) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)	USPAT; JPO	2004/03/21 23:41
19	BRS	730	(multi\$5) with (semiconductor or chip or die or IC) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue)	USPAT; JPO	2004/03/21 23:41
20	BRS	278	((multi\$5) with (semiconductor or chip or die or IC) and (xerogels or porous) same (insulat\$3 or dielectric or adhesive or glue)) not ((multi\$5) with (semiconductor or chip or die or IC) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue))	USPAT; JPO	2004/03/21 23:55
21	BRS	23	257/777 and (porous or xerogels) with (layer or film)	USPAT; JPO	2004/03/22 02:03
22	BRS	42	257/777 and (porous or xerogels)	USPAT; JPO	2004/03/22 00:08
23	BRS	19	(257/777 and (porous or xerogels)) not (257/777 and (porous or xerogels) with (layer or film))	USPAT; JPO	2004/03/22 00:17
24	BRS	1299	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous or polyimide) with (insulat\$3 or dielectric or adhesive or glue)	USPAT	2004/03/22 02:45

	Type	Hits	Search Text	DBs	Time Stamp
25	BRS	245	((lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous or polyimide) with (insulat\$3 or dielectric or adhesive or glue)) and 257/777	USPAT	2004/03/22 00:18
26	BRS	2045	(air or porous) with (polyimide)	USPAT; JPO	2004/03/22 02:04
27	BRS	1632	(air or porous) with (polyimide)	USPAT	2004/03/22 02:05
28	BRS	318	((air or porous) with (polyimide)) and "257"	USPAT	2004/03/22 02:04
29	BRS	23	(air or void) with porous with (polyimide)	USPAT	2004/03/22 02:10
30	BRS	6	((air or void) with porous with (polyimide)) and "257"	USPAT	2004/03/22 02:06
31	BRS	52	(air or void) same porous with (polyimide)	USPAT	2004/03/22 02:13
32	BRS	139	(air or void or pore) same porous with (polyimide)	USPAT	2004/03/22 02:13
33	BRS	25	((air or void or pore) same porous with (polyimide)) and "257"	USPAT	2004/03/22 02:32
34	BRS	74	257/777 and (adhesive or insulat\$3 or dielectric or glue) with air	USPAT	2004/03/22 02:40
35	BRS	0	257/777 and (adhesive or insulat\$3 or dielectric or glue) with (air or void or pore) with polyimide	USPAT	2004/03/22 02:41
36	BRS	6	257/777 and (adhesive or insulat\$3 or dielectric or glue) with (air or void or pore) same polyimide	USPAT	2004/03/22 02:41
37	BRS	11	257/777 and (adhesive or insulat\$3 or dielectric or glue) same (air or void or pore) same polyimide	USPAT	2004/03/22 02:44
38	BRS	1	257/777 and (adhesive or insulat\$3 or dielectric or glue) same (pore) same polyimide	USPAT	2004/03/22 03:06

	Type	Hits	Search Text	DBs	Time Stamp
39	BRS	4	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (xerogels or porous) with (insulat\$3 or dielectric or adhesive or glue) same polyimide	USPAT	2004/03/22 02:47
40	BRS	0	(lower or first or bottom) near (chip or die or IC or semiconductor) and (top or upper or second) near (chip or die or IC or semiconductor) and (insulat\$3 or dielectric or adhesive or glue) same polyimide with (pore)	USPAT	2004/03/22 02:47
41	BRS	1	(stack\$3 or mount\$3) with (semiconductor or chip or die or IC) and (insulat\$3 or dielectric or adhesive or glue) same polyimide with pore	JPO	2004/03/22 02:48
42	BRS	6	(stack\$3 or mount\$3) with (semiconductor or chip or die or IC) and (insulat\$3 or dielectric or adhesive or glue) same polyimide with pore	USPAT; JPO	2004/03/22 02:56
43	BRS	105	(stack\$3 or mount\$3) with (semiconductor or chip or die or IC) and (insulat\$3 or dielectric or adhesive or glue) same polyimide with (air or void)	USPAT; JPO	2004/03/22 02:56
44	BRS	464	257/777 and (adhesive or insulat\$3 or dielectric or glue) with polyimide	USPAT	2004/03/22 03:12
45	BRS	969	(xerogels or porous) with polyimide	USPAT; JPO	2004/03/22 03:19
46	BRS	21	(xerogels or porous) with polyimide with air	USPAT; JPO	2004/03/22 03:13
47	BRS	2	((xerogels or porous) with polyimide) and 257/777	USPAT; JPO	2004/03/22 03:19
48	BRS	13	"257" and foamed near polyimide	USPAT	2004/03/22 05:27
49	BRS	76	foamed near polyimide	USPAT	2004/03/22 05:31
50	BRS	380	foam\$3 near polyimide	USPAT	2004/03/22 05:31
51	BRS	88	(foam\$3 near polyimide) and (semicondcutor or die or chip or IC)	USPAT	2004/03/22 06:22

	Type	Hits	Search Text	DBs	Time Stamp
52	BRS	71	((foam\$3 near polyimide) and (semicondcutor or die or chip or IC)) and thickness	USPAT	2004/03/22 06:22
53	BRS	10	((foam\$3 near polyimide) and (semicondcutor or die or chip or IC)) and thickness with polyimide	USPAT	2004/03/22 06:35
54	BRS	12	(foam\$3 near polyimide) and thickness with (void or bubble or pore)	USPAT	2004/03/22 06:37
55	BRS	40	(foam\$3 near polyimide) and size with (void or bubble or pore)	USPAT	2004/03/22 06:39
56	BRS	56715	size with (void or bubble or pore)	USPAT	2004/03/22 06:39
57	BRS	44133	size with (pore)	USPAT	2004/03/22 06:40
58	BRS	2863	(size with (pore)) and "257"	USPAT	2004/03/22 06:39
59	BRS	7956	size with (pore) with porous	USPAT	2004/03/22 06:40
60	BRS	196	size with (pore) with porous near (layer or film) and (semiconductor or die or chip or IC)	USPAT	2004/03/22 06:41
61	BRS	3	size with (pore) with porous near (layer or film) and (semiconductor or die or chip or IC) with 0.1 near microns	USPAT	2004/03/22 06:41